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|---|---------|---------------------------|
| SANYO | No.3813 | 2SJ228 |
| | | P-Channel MOS Silicon FET |
| Very High-Speed Switching Applications | | |

Features

- Small ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Meets radial taping.

Absolute Maximum Ratings at Ta = 25°C

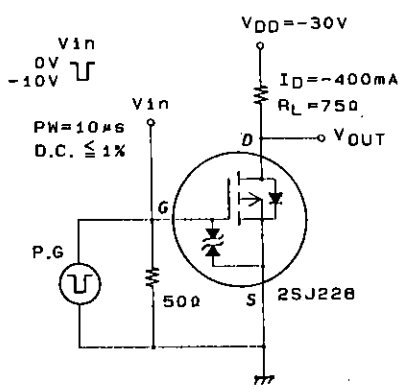
| | | | |
|-----------------------------|------------------|-------------|------|
| | | | unit |
| Drain to Source Voltage | V _{DSS} | -60 | V |
| Gate to Source Voltage | V _{GSS} | ±15 | V |
| Drain Current (DC) | I _D | -0.8 | A |
| Drain Current (Pulse) | I _{DP} | -3.2 | A |
| Allowable Power Dissipation | P _D | 1 | W |
| Channel Temperature | T _{ch} | 150 | °C |
| Storage Temperature | T _{stg} | -55 to +150 | °C |

PW ≤ 10μs, duty cycle ≤ 1%

Electrical Characteristics at Ta = 25°C

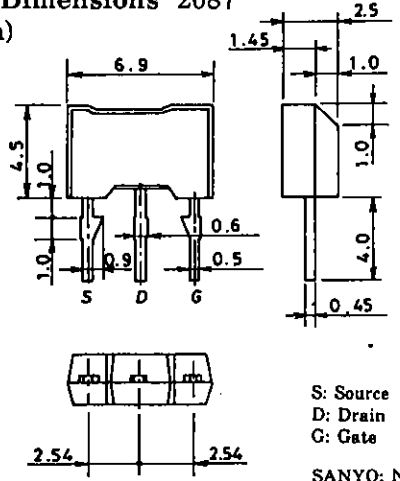
| | | | min | typ | max | |
|---|----------------------|---|------|------|------|----|
| D-S Breakdown Voltage | V _{(BR)DSS} | I _D = -1mA, V _{GS} = 0 | -60 | | | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = -60V, V _{GS} = 0 | | | -100 | μA |
| Gate to Source Leakage Current | I _{GSS} | V _{GS} = ±12V, V _{DS} = 0 | | | ±10 | μA |
| Cutoff Voltage | V _{GS(off)} | V _{DS} = -10V, I _D = -1mA | -1.0 | | -2.0 | V |
| Forward Transfer Admittance | Y _{fs} | V _{DS} = -10V, I _D = -400mA | 0.5 | 0.9 | | S |
| Static Drain to Source on State Resistance | R _{DS(on)} | I _D = -400mA, V _{GS} = -10V | | 0.9 | 1.2 | Ω |
| | R _{DS(on)} | I _D = -400mA, V _{GS} = -4V | | 1.2 | 1.6 | Ω |
| Input Capacitance | C _{iss} | V _{DS} = -20V, f = 1MHz | | 160 | | pF |
| Output Capacitance | C _{oss} | V _{DS} = -20V, f = 1MHz | | 60 | | pF |
| Reverse Transfer Capacitance | C _{rss} | V _{DS} = -20V, f = 1MHz | | 10 | | pF |
| Turn-ON Delay Time | t _{d(on)} | See specified Test Circuit. | | 10 | | ns |
| Rise Time | t _r | " | | 12 | | ns |
| Turn-OFF Delay Time | t _{d(off)} | " | | 75 | | ns |
| Fall Time | t _f | " | | 30 | | ns |
| Diode Forward Voltage | V _{SD} | I _S = -800mA, V _{GS} = 0 | | -0.9 | | V |

Switching Time Test Circuit

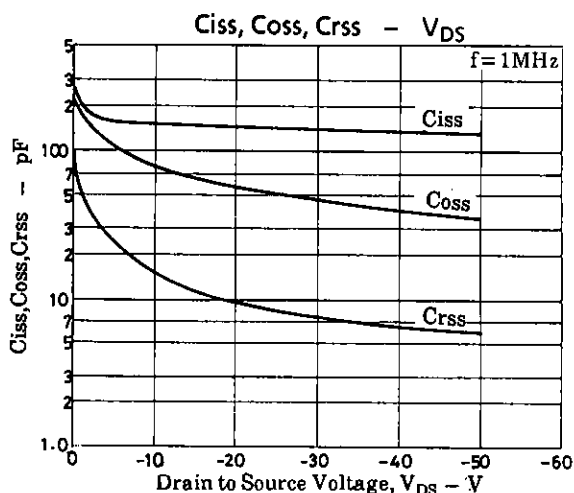
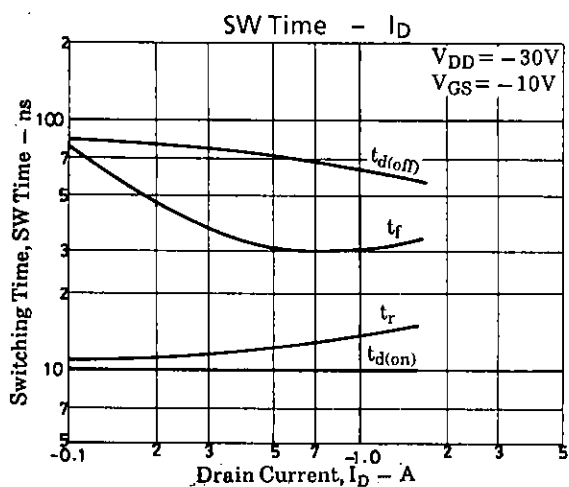
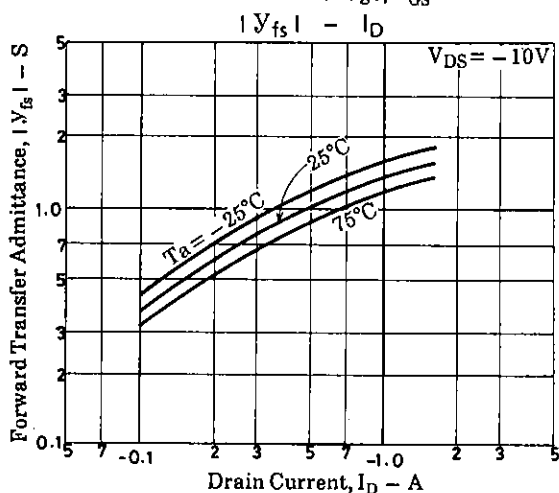
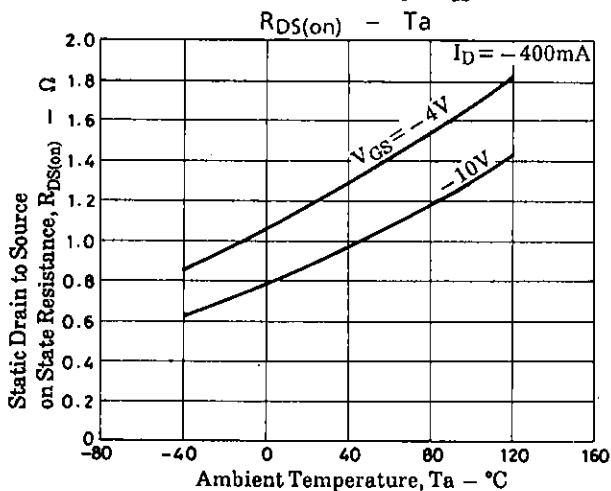
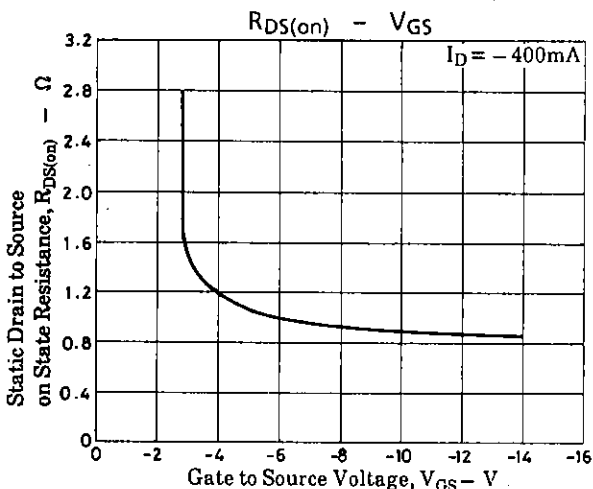
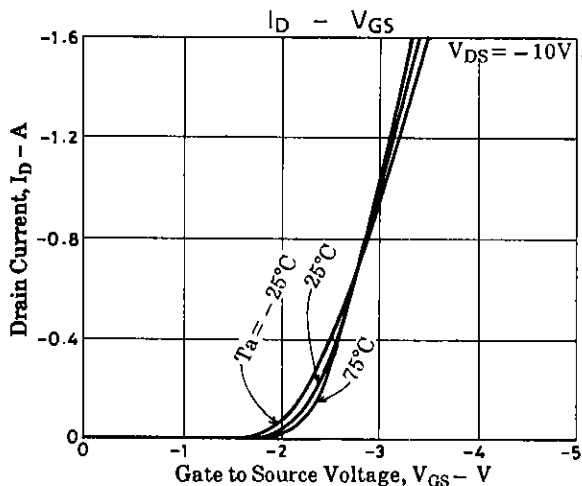
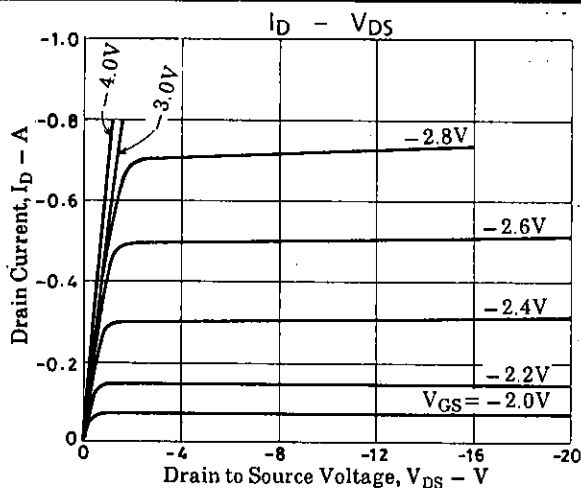
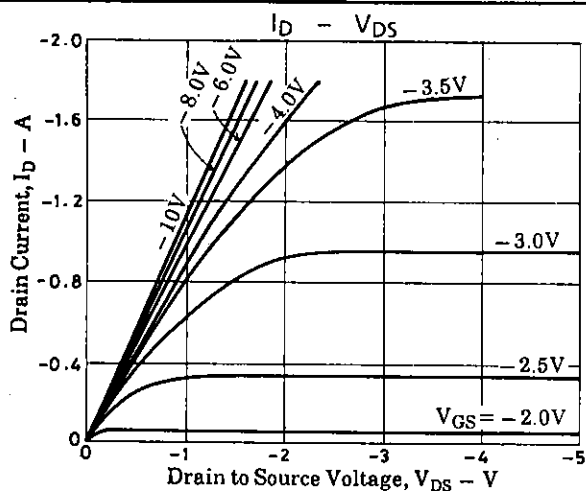


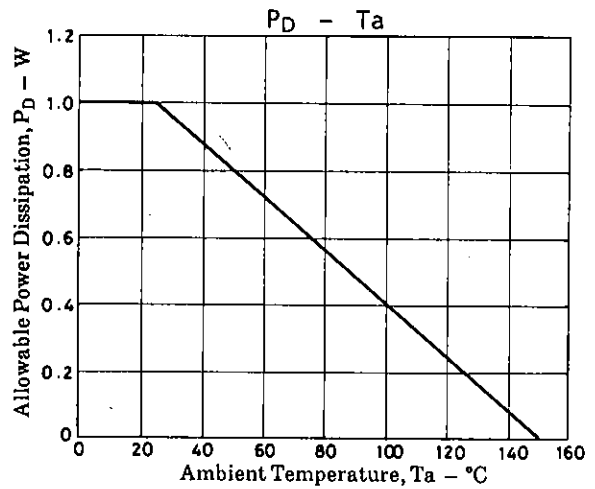
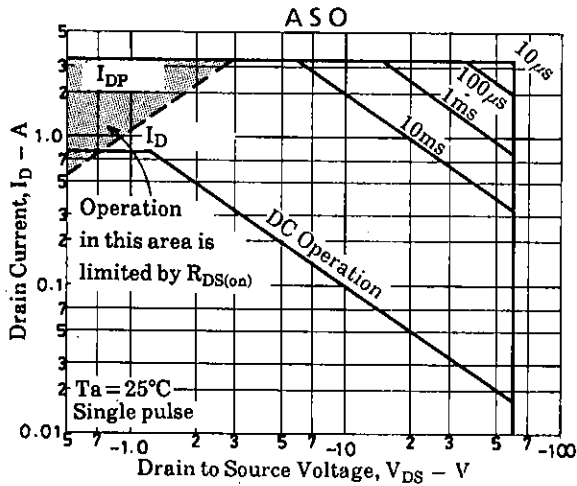
Package Dimensions 2087

(unit : mm)



S: Source
D: Drain
G: Gate
SANYO: NMP





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